

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### Listing of Claims:

Claim 1 (currently amended): A ~~sputtering target, comprising a~~ copper alloy sputtering target ~~containing~~ consisting of 0.01 to less than 0.5wt% of Al, at least one of Mn or Si or both in a total amount of 0.03wtppm to 0.25wtppm, ~~and~~ at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 1.0wtppm or less, and a remainder of copper and inevitable impurities.

Claims 2-15 (canceled).

Claim 16 (previously presented): A sputtering target according to claim 1, wherein said copper alloy sputtering target contains 0.05 to 0.2wt% of Al.

Claim 17 (previously presented): A sputtering target according to claim 16, wherein said total amount of said at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As is 0.3wtppm or less.

Claim 18 (currently amended): A sputtering target according to claim 17, wherein said inevitable impurities, excluding gas components, in said copper alloy sputtering target are 1wtppm or less.

Claim 19 (previously presented): A sputtering target according to claim 1, wherein said total amount of said at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As is 0.13wtppm to 1.0wtppm.

Claim 20 (previously presented): A sputtering target according to claim 19, wherein said total amount of said at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As does not exceed 0.5wtppm.

Claim 21 (previously presented): A sputtering target according to claim 20, wherein said total amount of said at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As does not exceed 0.3wtppm.

Claim 22 (currently amended): A sputtering target according to claim 1, wherein said inevitable impurities, excluding gas components, in said copper alloy sputtering target are 10wtppm or less.

Claim 23 (previously amended): A sputtering target according to claim 22, wherein said inevitable impurities, excluding gas components, are 1wtppm or less.

Claim 24 (currently amended): A sputtering target according to claim 1, wherein said inevitable impurities of said copper alloy sputtering target ~~contains~~ include: 0.05wtppm or less of Na and K, respectively; ~~wherein said copper alloy sputtering target contains 1 wtppb or less of U~~

and Th, respectively; and ~~wherein said copper alloy sputtering target contains 5wtppm or less of~~  
oxygen, 2wtppm or less of nitrogen, and 2wtppm or less of carbon.

Claim 25 (currently amended): A sputtering target according to claim 1, wherein said  
inevitable impurities of said copper alloy sputtering target contains include: 0.02wtppm or less of  
Na and K, respectively; ~~wherein said copper alloy sputtering target contains 0.5wtppb or less of~~  
U and Th, respectively; and ~~wherein said copper alloy sputtering target contains 1wtppm or less~~  
of oxygen, 1wtppm or less of nitrogen, and 1wtppm or less of carbon.

Claim 26 (previously presented): A sputtering target according to claim 1, wherein said  
copper alloy sputtering target has an average crystal grain size of 100 $\mu$ m or less and an average  
grain size variation within  $\pm 20\%$ .

Claims 27-34 (canceled).

Claim 35 (previously presented): A copper alloy sputtering target for forming a thin film  
seed layer for semiconductor wiring, consisting of:

0.01 to less than 0.5wt% of Al for preventing coagulation upon plating on the  
seed layer;

at least one of Mn or Si or both in a total amount of 0.03wtppm to 0.25wtppm for  
improving oxidation resistance;

at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 0.13wtppm to 1.0wtppm for improving oxidation resistance; and  
a remainder being copper.

Claim 36 (previously presented): A copper alloy sputtering target according to claim 35 wherein said at least one of Mn or Si or both is Mn.

Claim 37 (previously presented): A copper alloy sputtering target according to claim 35, wherein said copper alloy sputtering target contains 0.05 to 0.2wt% of Al, and wherein said total amount of said at least one element selected from the group consisting of Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As is 0.13wtppm to 0.3wtppm.

Claim 38 (previously presented): A copper alloy sputtering target according to claim 35, wherein said copper alloy sputtering target has an average crystal grain size of 100µm or less and an average grain size variation within  $\pm 20\%$ .

Claims 39-42 (canceled).